

International **IR** Rectifier

HEXFRED™

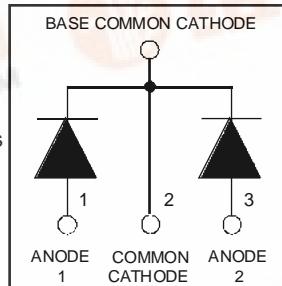
PD -2.460A

HFA70NK60C

Ultrafast, Soft Recovery Diode

Features

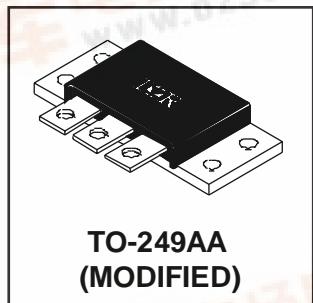
- Reduced RFI and EMI
- Reduced Snubbing
- Extensive Characterization of Recovery Parameters



$V_R = 600V$
$V_F(\text{typ.})^{\circledcirc} = 1.2V$
$I_{F(AV)} = 70A$
$Q_{rr} (\text{typ.}) = 210nC$
$I_{RRM} (\text{typ.}) = 6A$
$t_{rr} (\text{typ.}) = 30ns$
$di_{(rec)M}/dt (\text{typ.})^{\circledcirc} = 180A/\mu s$

Description

HEXFRED™ diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems. An extensive characterization of the recovery behavior for different values of current, temperature and di/dt simplifies the calculations of losses in the operating conditions. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for power converters, motors drives and other applications where switching losses are significant portion of the total losses.



Absolute Maximum Ratings (per Leg)

	Parameter	Max.	Units
V_R	Cathode-to-Anode Voltage	600	V
$I_F @ T_C = 25^\circ C$	Continuous Forward Current	59	
$I_F @ T_C = 100^\circ C$	Continuous Forward Current	29	
I_{FSM}	Single Pulse Forward Current \circledcirc	200	A
I_{AS}	Maximum Single Pulse Avalanche Current \circledcirc	2.0	
E_{AS}	Non-Repetitive Avalanche Energy \circledcirc	220	μJ
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	160	
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	63	
T_J	Operating Junction and		
T_{STG}	Storage Temperature Range	-55 to +150	$^\circ C$
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	

Thermal - Mechanical Characteristics

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case, Single Leg Conducting	---	---	0.80	$^\circ C/W$
	Junction-to-Case, Both Legs Conducting	---	---	0.40	
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	---	0.10	---	
W_t	Weight	---	58 (2.0)	---	$g (oz)$
	Mounting Torque	35 (4.0)	---	50 (5.7)	$lbf \cdot in$ (N·m)

Note: \circledcirc Limited by junction temperature

\circledcirc $L = 100\mu H$, duty cycle limited by max T_J

\circledcirc $125^\circ C$

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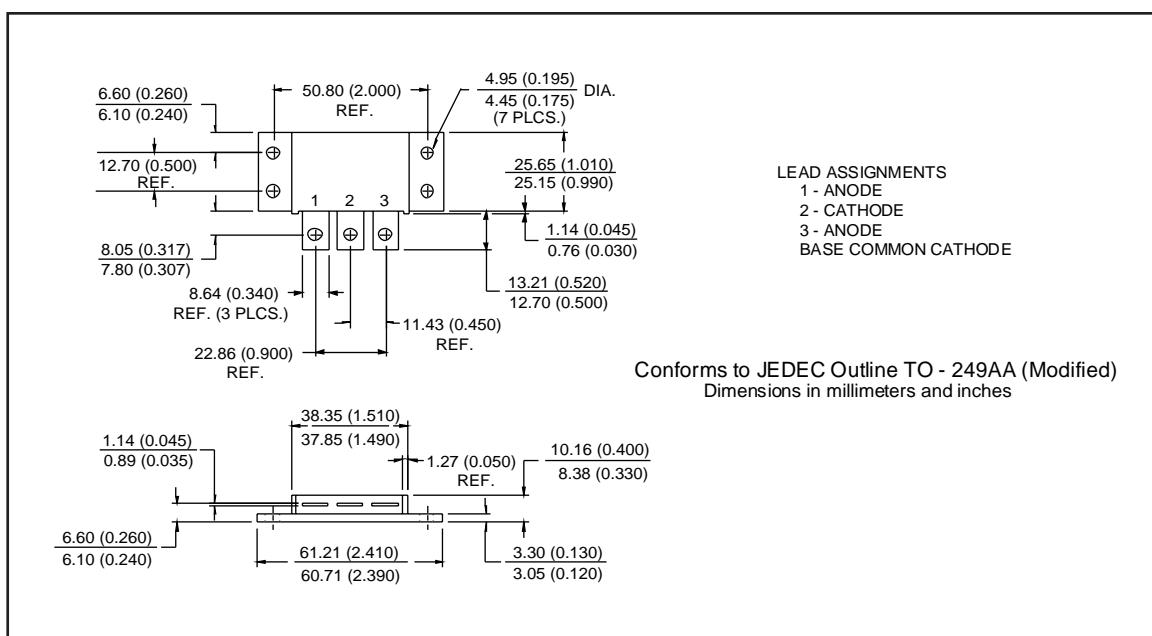
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Electrical Characteristics (per Leg) @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
V_{BR}	Cathode Anode Breakdown Voltage	600	—	—	V	$I_R = 100\mu\text{A}$
V_{FM}	Max Forward Voltage	—	1.3	1.5	V	$I_F = 35\text{A}$
		—	1.5	1.7	V	$I_F = 70\text{A}$
		—	1.2	1.4	V	$I_F = 35\text{A}, T_J = 125^\circ\text{C}$
		—	2.0	10	μA	$V_R = V_R \text{ Rated}$
I_{RM}	Max Reverse Leakage Current	—	0.50	2.0	mA	$T_J = 125^\circ\text{C}, V_R = 480\text{V}$
		—	68	100	pF	$V_R = 200\text{V}$
C_T	Junction Capacitance	—	9.2	—	nH	See Fig. 3
L_S	Series Inductance	—	—	—	—	Lead to lead 5mm from package body

Dynamic Recovery Characteristics (per Leg) @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
t_{rr}	Reverse Recovery Time	—	30	—	ns	$I_F = 1.0\text{A}, dI/dt = 200\text{A}/\mu\text{s}, V_R = 30\text{V}$
		—	70	110	ns	$T_J = 25^\circ\text{C}$ See Fig. 5
		—	115	180	ns	$T_J = 125^\circ\text{C}$ 5
I_{RRM1}	Peak Recovery Current	—	6.0	11	A	$T_J = 25^\circ\text{C}$ See Fig. 6
		—	9.0	16	A	$T_J = 125^\circ\text{C}$ 6
Q_{rr1}	Reverse Recovery Charge	—	210	580	nC	$T_J = 25^\circ\text{C}$ See Fig. 7
		—	520	1400	nC	$T_J = 125^\circ\text{C}$ 7
$di_{(rec)M}/dt_1$	Peak Rate of Fall of Recovery Current During t_b	—	280	—	A/ μs	$T_J = 25^\circ\text{C}$ See Fig. 8
		—	180	—	A/ μs	$T_J = 125^\circ\text{C}$ 8



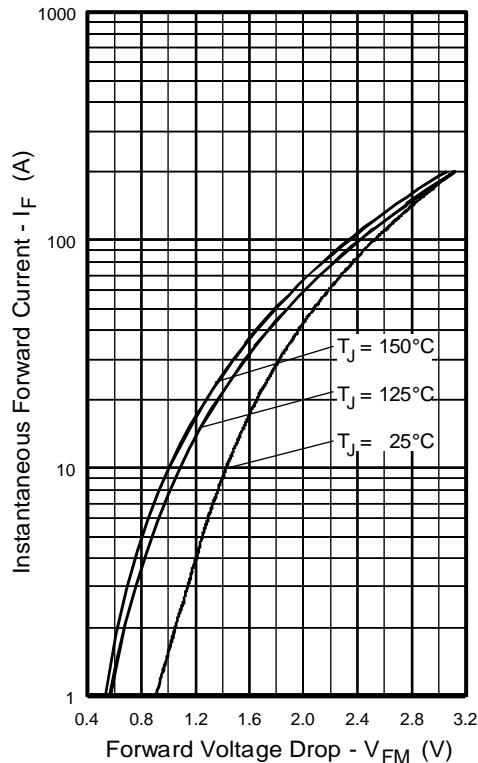


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current, (per Leg)

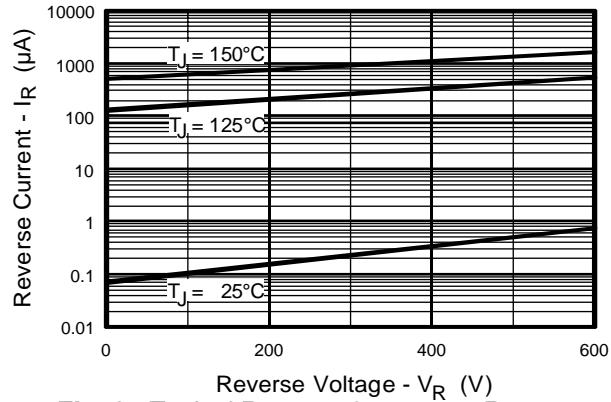


Fig. 2 - Typical Reverse Current vs. Reverse Voltage, (per Leg)

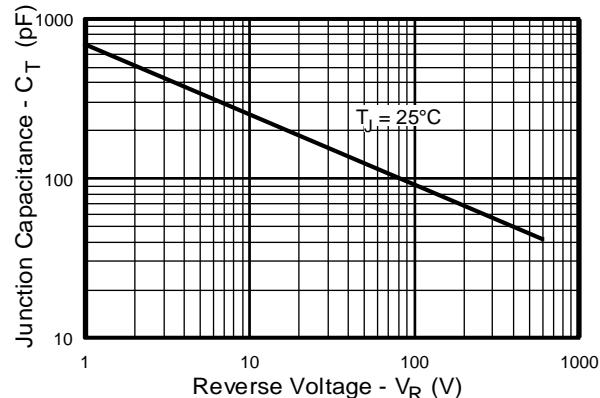


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage, (per Leg)

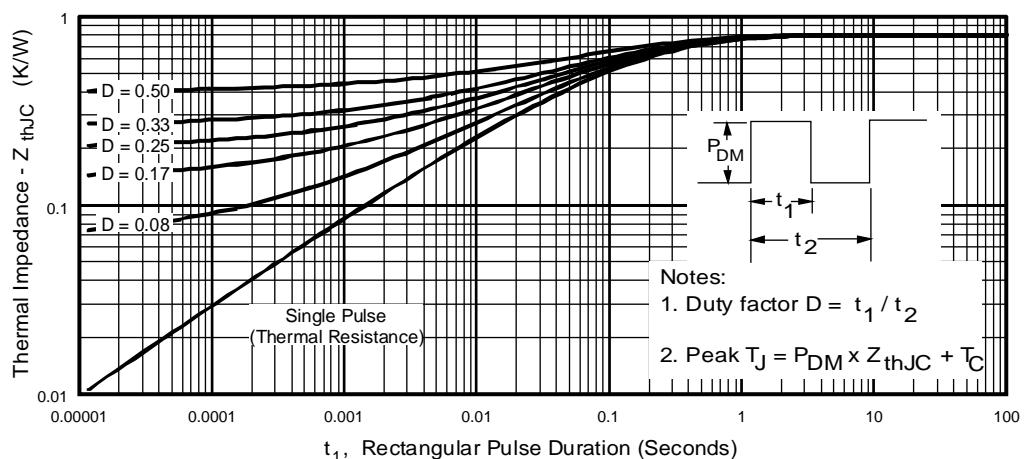


Fig. 4 - Maximum Thermal Impedance Z_{thjc} Characteristics, (per Leg)

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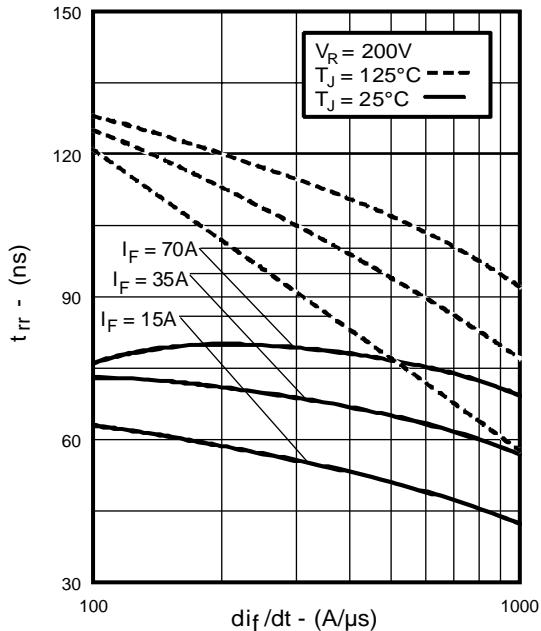


Fig. 5 - Typical Reverse Recovery vs. di_f/dt , (per Leg)

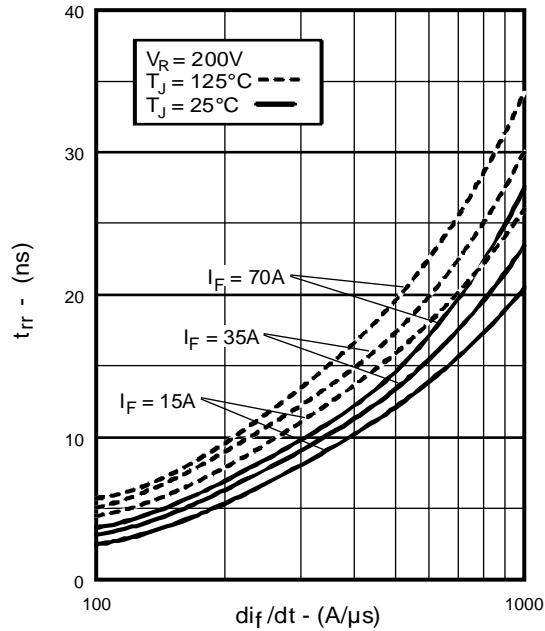


Fig. 6 - Typical Recovery Current vs. di_f/dt , (per Leg)

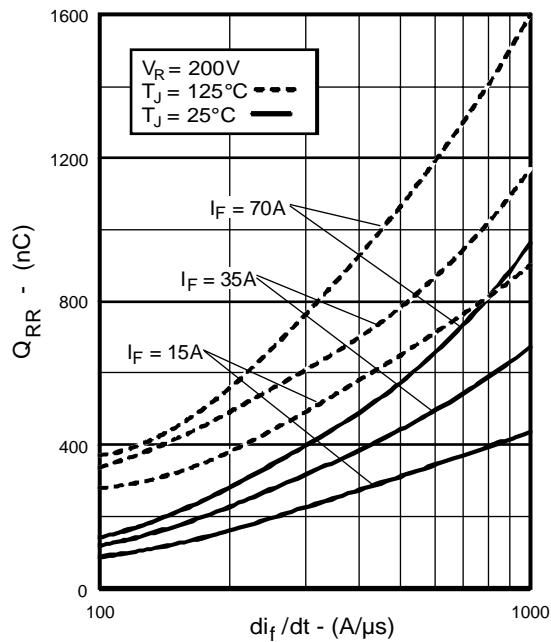


Fig. 7 - Typical Stored Charge vs. di_f/dt , (per Leg)

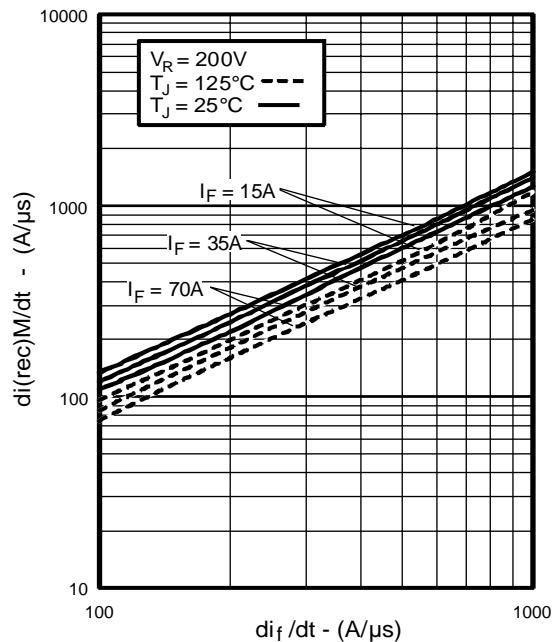


Fig. 8 - Typical $d(di_{rec})/dt$ vs. di_f/dt , (per Leg)

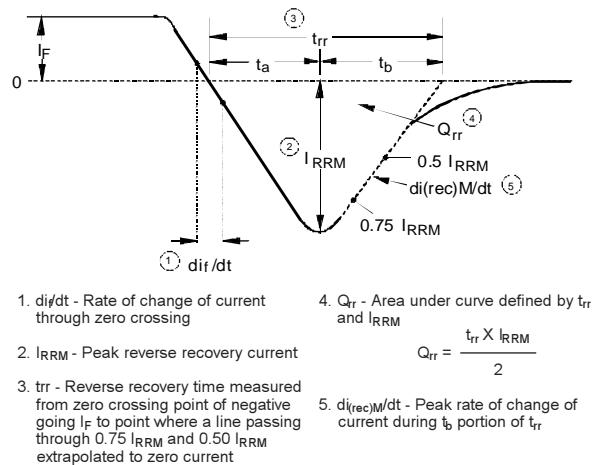
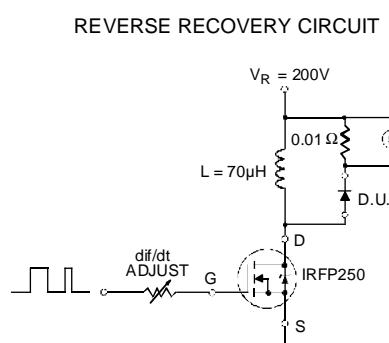


Fig. 9 - Reverse Recovery Parameter Test Circuit

Fig. 10 - Reverse Recovery Waveform and Definitions

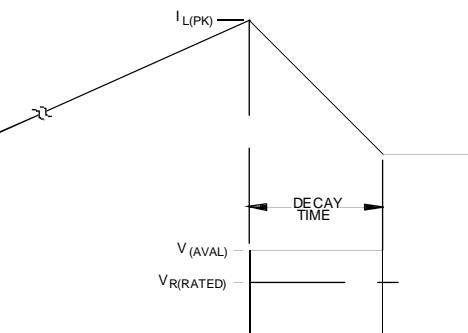
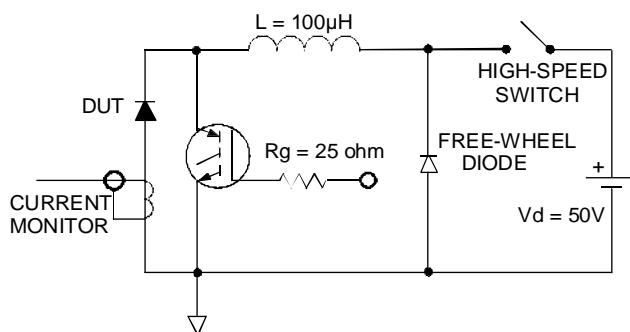


Fig. 11 - Avalanche Test Circuit and Waveforms

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